

2N3637

PNP SILICON TRANSISTOR



TO-39 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3637 is a PNP Silicon Transistor, mounted in a hermetically sealed TO-39 package, designed for general purpose amplifier and high voltage switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current
 Power Dissipation
 Power Dissipation ($T_C=25^\circ\text{C}$)
 Operating and Storage Junction Temperature
 Thermal Resistance
 Thermal Resistance

| SYMBOL | | UNITS |
|----------------|-------------|--------------------|
| V_{CB0} | 175 | V |
| V_{CEO} | 175 | V |
| V_{EBO} | 5.0 | V |
| I_C | 1.0 | A |
| P_D | 1.0 | W |
| P_D | 5.0 | W |
| T_J, T_{stg} | -65 to +200 | $^\circ\text{C}$ |
| θ_{JA} | 175 | $^\circ\text{C/W}$ |
| θ_{JC} | 35 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|---------------|---|------|-----|-------|
| I_{CBO} | $V_{CB}=100\text{V}$ | | 100 | nA |
| I_{EBO} | $V_{EB}=3.0\text{V}$ | | 50 | nA |
| BV_{CBO} | $I_C=100\mu\text{A}$ | 175 | | V |
| BV_{CEO} | $I_C=10\text{mA}$ | 175 | | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ | 5.0 | | V |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 0.3 | V |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | | 0.5 | V |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 0.8 | V |
| $V_{BE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | 0.65 | 0.9 | V |
| h_{FE} | $V_{CE}=10\text{V}, I_C=0.1\text{mA}$ | 80 | | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=1.0\text{mA}$ | 90 | | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=10\text{mA}$ | 100 | | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=50\text{mA}$ | 100 | 300 | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=150\text{mA}$ | 50 | | |
| f_T | $V_{CE}=30\text{V}, I_C=30\text{mA}, f=100\text{MHz}$ | 200 | | MHz |
| C_{ob} | $V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$ | | 10 | pF |
| C_{ib} | $V_{EB}=1.0\text{V}, I_C=0, f=1.0\text{MHz}$ | | 75 | pF |
| t_{on} | $V_{CC}=100\text{V}, V_{BE}=4.0\text{V}, I_C=50\text{mA}, I_{B1}=I_{B2}=5.0\text{mA}$ | | 400 | ns |
| t_{off} | $V_{CC}=100\text{V}, V_{BE}=4.0\text{V}, I_C=50\text{mA}, I_{B1}=I_{B2}=5.0\text{mA}$ | | 600 | ns |

R0 (22-November 2010)

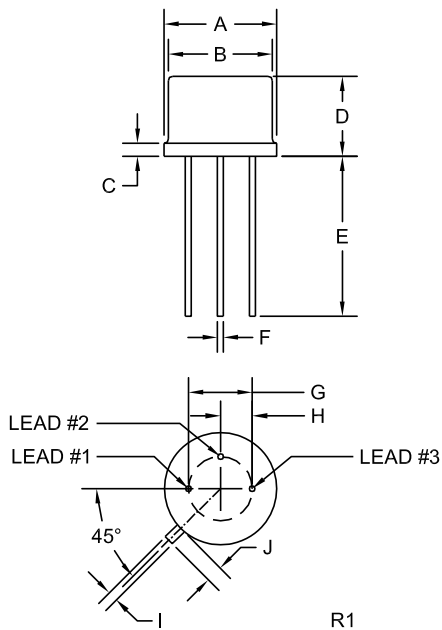
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|----------|---|-----|------|------------------|
| h_{ie} | $V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$ | 200 | 1200 | Ω |
| h_{re} | $V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$ | | 3.0 | $\times 10^{-4}$ |
| h_{fe} | $V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$ | 80 | 320 | |
| h_{oe} | $V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$ | | 200 | μS |
| NF | $V_{CE}=10\text{V}, I_C=0.5\text{mA}, f=1.0\text{kHz}, R_S=1.0\text{k}\Omega$ | | 3.0 | dB |

TO-39 CASE - MECHANICAL OUTLINE



| SYMBOL | DIMENSIONS | | | |
|---------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A (DIA) | 0.335 | 0.370 | 8.51 | 9.40 |
| B (DIA) | 0.315 | 0.335 | 8.00 | 8.51 |
| C | - | 0.040 | - | 1.02 |
| D | 0.240 | 0.260 | 6.10 | 6.60 |
| E | 0.500 | - | 12.70 | - |
| F (DIA) | 0.016 | 0.021 | 0.41 | 0.53 |
| G (DIA) | 0.200 | | 5.08 | |
| H | 0.100 | | 2.54 | |
| I | 0.028 | 0.034 | 0.71 | 0.86 |
| J | 0.029 | 0.045 | 0.74 | 1.14 |

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R0 (22-November 2010)